Meng Xiao

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/8683740/publications.pdf

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10	307	6	9
papers	citations	h-index	g-index
10	10	10	371 citing authors
all docs	docs citations	times ranked	

#	Article	IF	CITATIONS
1	Understanding efficiency droop effect in InGaN/GaN multiple-quantum-well blue light-emitting diodes with different degree of carrier localization. Applied Physics Letters, 2010, 97, .	3.3	104
2	An improved carrier rate model to evaluate internal quantum efficiency and analyze efficiency droop origin of InGaN based light-emitting diodes. Journal of Applied Physics, 2012, 112, 023107.	2.5	53
3	Abnormal Stranski–Krastanov Mode Growth of Green InGaN Quantum Dots: Morphology, Optical Properties, and Applications in Light-Emitting Devices. ACS Applied Materials & Devices, 2019, 11, 1228-1238.	8.0	51
4	Study on efficiency droop in $InGaN/GaN$ light-emitting diodes based on differential carrier lifetime analysis. Applied Physics Letters, 2016, 108, .	3.3	40
5	A Review on Experimental Measurements for Understanding Efficiency Droop in InGaN-Based Light-Emitting Diodes. Materials, 2017, 10, 1233.	2.9	37
6	Influence of dislocation density on internal quantum efficiency of GaN-based semiconductors. AIP Advances, 2017, 7, 035321.	1.3	11
7	The influences of sputtered AlN buffer layer on AllnGaN based blue and nearâ€ultraviolet light emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600714.	1.8	6
8	A Method to Obtain Auger Recombination Coefficient in an InGaN-Based Blue Light-Emitting Diode. Chinese Physics Letters, 2017, 34, 017301.	3.3	3
9	High-Particle-Density YAG:Ce Phosphor Coating for High Power Laser Lighting. Journal of Electronic Packaging, Transactions of the ASME, 2020, 142, .	1.8	2
10	Carrier lifetimes in polar InGaN-based LEDs. , 2018, , .		0